TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIV)

TK100F04K3

Swiching Regulator, DC-DC Converter Applications Motor Drive Applications

• Low drain-source ON resistance: RDS (ON) = $2.5 \text{ m}\Omega$ (typ.)

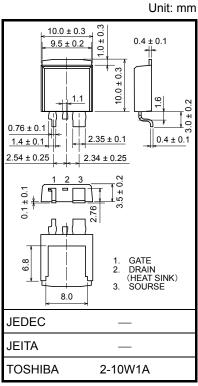
• High forward transfer admittance: $|Y_{fs}| = 174 \text{ S (typ.)}$

• Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$

• Enhancement-model: $V_{th} = 3.0 \text{ to } 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

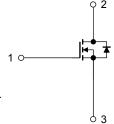
Characteristics			Symbol	Rating	Unit	
Drain-source voltage			V_{DSS}	40	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)			V_{DGR}	40	V	
Gate-source voltage			V _{GSS}	±20	V	
Drain current	DC	(Note 1)	I _D	100	Α	
	Pulse	(Note 1)	I _{DP}	300	A	
Drain power dissipation (Tc = 25°C)			P _D	180	W	
Single pulse avalanche energy (Note 2)			E _{AS}	125	mJ	
Avalanche current			I _{AR}	100	Α	
Repetitive avalanche energy (Note 3)			E _{AR}	18	mJ	
Channel temperature (Note 4)		T _{ch}	175	°C		
Storage temperature range (Note 4)			T _{stg}	–55 to 175	°C	



Weight: 1.07 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	0.83	°C/W	



Note 1: Please use devices on condition that the channel temperature is below 175°C.

Note 2: $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$, $L = 13 \,\mu\text{H}$, $R_G = 25 \,\Omega$, $I_{AR} = 100 \,\text{A}$

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

Note 4: 175°C refers to AEC-Q101.

Note 5: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic sensitive device. Please handle with caution

2009-09-29



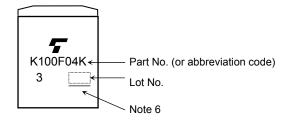
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА	
Drain cut-OFF cu	rrent	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	_	_	10	μΑ	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	40	_	_	V	
		V (BR) DSX	$I_D = 10$ mA, $V_{GS} = -20$ V	20	_	_	V	
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	3.0	_	4.0	V	
Drain-source ON resistance		R _{DS} (ON)	V _{GS} = 10 V, I _D = 50 A	_	2.5	3.0	mΩ	
Forward transfer admittance		Y _{fS}	V _{DS} = 10 V, I _D = 50 A	87	174	_	S	
Input capacitance		C _{iss}	V _{DS} = 10V, V _{GS} = 0 V, f = 1 MHz	_	4500	_	pF	
Reverse transfer capacitance		C _{rss}		_	900	_		
Output capacitance		C _{oss}			1100	_		
Switching time -	Rise time	t _r	10 V		21		- ns	
	Turn-ON time	t _{on}	$\begin{array}{c c} 10 \text{ V} & \text{ID} = 50 \text{ A} \\ \text{VGS} & \text{VOUT} \\ \text{O} & \text{V} & \text{RL} = 0.4 \Omega \end{array}$	_	37	_		
	Fall time	t _f	V _{DD} ≈ 20 V	_	31	_		
	Turn-OFF time	t _{off}	Duty \leq 1%, $t_W = 10 \mu s$	_	75	_		
Total gate charge (gate-source plus gate-drain)		Qg		_	102	_	nC	
Gate-source charge		Q _{gs}	$V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 100 \text{ A}$	_	56	_		
Gate-drain ("miller") charge		Q _{gd}		_	46	_		

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	_	_	_	100	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_			300	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 100 A, V _{GS} = 0 V			-1.2	V
Reverse recovery time	t _{rr}	$I_{DR} = 100 \text{ A}, V_{GS} = 0 \text{ V},$	_	61	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 50 A/μs	_	49	_	nC

Marking



Note 6: A line under a Lot No. identifies the indication of product Labels. [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



Moisture-Proof Packing

The TK100F04K3 is packed in a moisture-proof laminated aluminum bag.

Precautions for Transportation and Storage

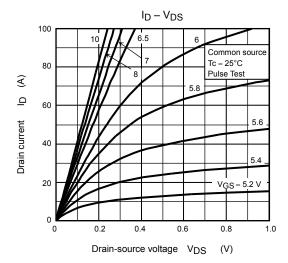
- (1) Avoid excessive vibration during transportation.
- (2) Do not toss or drop the packed devices to avoid ripping of the bag.
- (3) After opening the moisture-proof bag, the devices should be assembled within two weeks in an environment of 5°C to 30°C and RH70% or below. Perform reflow at most twice.
- (4) The moisture-proof bag may be stored unopened for up to 12 months at 5°C to 30°C and RH90% or below.
- (5) If, upon opening the bag, the moisture indicator card shows humidity of 30% or above (the color of the 30% dot has changed from blue to pink) or the expiration date has passed, the devices should be baked as follows:

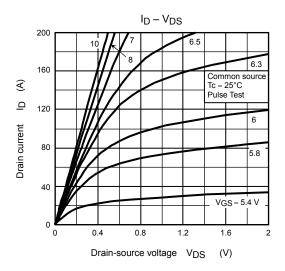
 Baking conditions: 125°C for 48 hours.

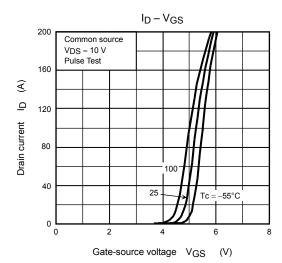
Since the tape materials are not heat-proof, devices should be placed on either heat-proof trays or aluminum magazines when baking.

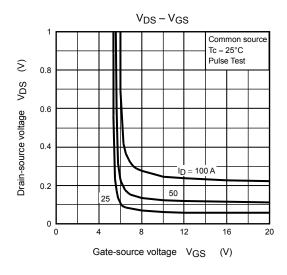


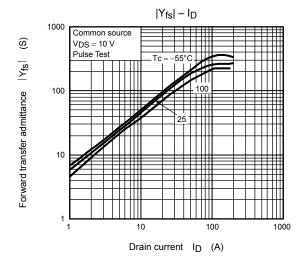
The humidity indicator shows an approximate ambient humidity at 25°C. If the ambient humidity is below 30%, the color of all the indicator dots is blue. If, upon opening the bag, the color of the 30% dot has changed from blue to pink, the devices should be baked before assembly.

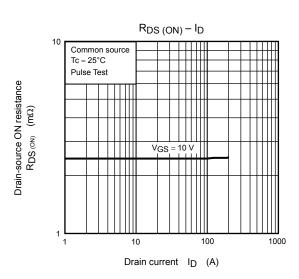


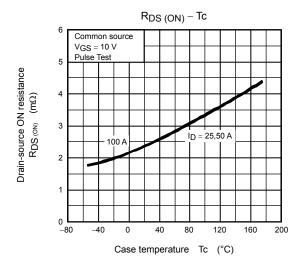


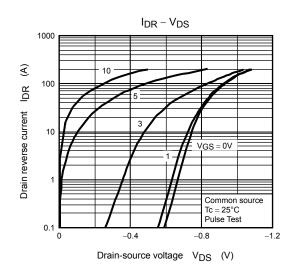


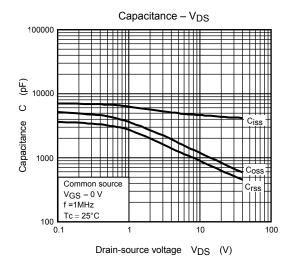


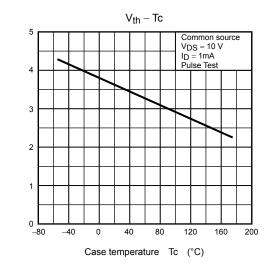


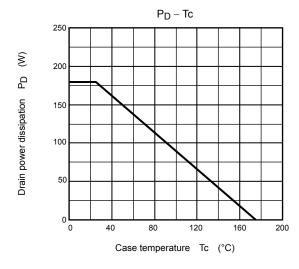


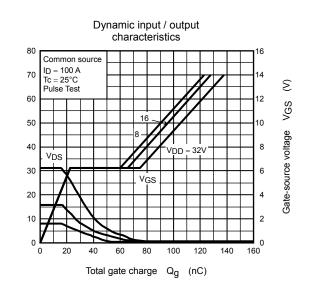










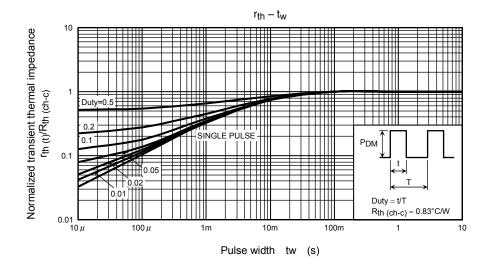


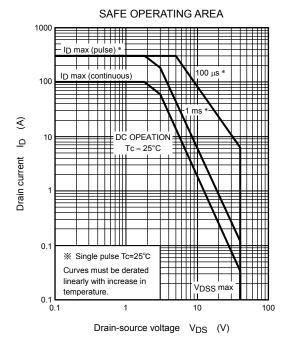
V_{th} (V)

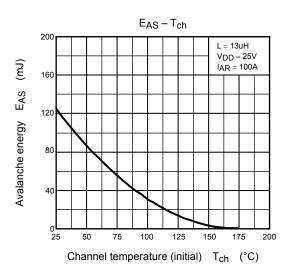
Gate threshold voltage

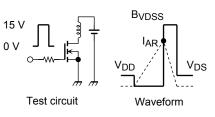
S

Drain-source voltage VDS









$$R_G = 25 \Omega$$

 $V_{DD} = 25 V, L = 13 \mu H$

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$$E = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right)$$

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